

GALLIUM Nitride Wafer

Product Description

Gallium nitride (GaN) is used as the wide band gap material for next generation power semiconductors and high frequency devices. Gallium Nitride is an upcoming alternate material to pure silicon in the field of electronics and semiconductors. Gallium Nitride is quickly replacing the existing silicon technology and becoming the most of the power semiconductor applications.

- Totally customized
- Low and medium volumes
- Any diameter
- Any orientations
- Any thickness

Typical Properties

Diameter	:	2", (Totally customized)
Thickness	:	4 μ m \pm 1 μ m, 4 μ m \pm 1 μ m (Totally customized)
Doping	:	Undoped, silicon
Thickness of Sapphire	:	650 \pm 25 μ m for 4inch , 650 \pm 25 μ m for 4 inch (Totally customized)
Substrate	:	Sapphire
Orientation	:	C-axis (001) \pm 1.0o (Totally customized)
TTV	:	\leq 10 μ m, \leq 15 μ m
Edge Profile	:	Rounded

Applications

- ✓ Semiconductor device
- ✓ Microelectronics
- ✓ Sensor
- ✓ Solar cell
- ✓ IR optics
- ✓ Various LED's
- ✓ Laser diodes: blue LD
- ✓ Power electronic devices
- ✓ High frequency electronic devices



2"
Inch

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